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wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film.

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2. (Amended) A contact structure of claim 1 wherein the insulating film is a resin film.

4. (Amended) A contact structure of claim 1 wherein the metallic film comprises Al.

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5. (Amended) A contact structure of claim 1 wherein the metallic film comprises W.

6. (Amended) A contact structure of claim 1 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

8. (Amended) A contact structure of claim 1 wherein the transparent conductive film comprises zinc oxide.

9. (Amended) A contact structure of claim 1 wherein the transparent conductive film comprises zinc oxide and indium oxide.

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10. (Amended) A contact structure comprising:
a first substrate;
a second substrate;
a connecting wiring over said first substrate;
a wiring under the second substrate;
an anisotropic conductive film comprising a grain plated with at least one material selected from the group consisting of chromium and gold; and
wherein said connecting wiring over said substrate and said wiring under said second substrate are electrically connected by said anisotropic conductive film,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,

wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film, and

wherein said metallic film is not in contact with said grain in said anisotropic conductive film.

11. (Amended) A contact structure of claim 10 wherein the insulating film is a resin film.

13. (Amended) A contact structure of claim 10 wherein the metallic film comprises Al.

14. (Amended) A contact structure of claim 10 wherein the metallic film comprises W.

17. (Amended) A contact structure of claim 10 wherein the transparent conductive film comprises zinc oxide.

18. (Amended) A contact structure of claim 10 wherein the transparent conductive film comprises zinc oxide and indium oxide.

19. (Amended) A semiconductor device comprising:
a circuit comprising a thin film transistor over a substrate; and
a connecting wiring over said substrate for connecting said circuit to another circuit,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,

wherein a side surface of said metallic film is covered with an insulating film along the length direction and the width direction of said lamination film, and

wherein said lamination film has a taper shape.

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20. (Amended) A semiconductor device of claim 19 wherein the insulating film is formed from the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

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22. (Amended) A semiconductor device of claim 19 wherein the insulating film is a resin film.

24. (Amended) A contact structure of claim 19 wherein the metallic film comprises Al.

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25. (Amended) A contact structure of claim 19 wherein the metallic film comprises W.

26. (Amended) A semiconductor device of claim 19 wherein the metallic film is a lamination film formed of a W layer, and a layer comprising W and N.

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28. (Amended) A contact structure of claim 19 wherein the transparent conductive film comprises zinc oxide.

29. (Amended) A contact structure of claim 19 wherein the transparent conductive film comprises zinc oxide and indium oxide.

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31. (Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing said first substrate;
a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit; and
an insulating film in contact with a side surface of said metallic film,
wherein said connecting wiring and said insulating film are formed over said first substrate,

wherein said insulating film is formed along with the length direction and the width direction of said lamination film, and

wherein said connecting wiring has a taper shape.

32. (Amended) A semiconductor device of claim 31 wherein the insulating film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

34. (Amended) A semiconductor device of claim 31 wherein the insulating film is a resin film.

36. (Amended) A contact structure of claim 31 wherein the metallic film comprises Al.

37. (Amended) A contact structure of claim 31 wherein the metallic film comprises W.

38. (Amended) A contact structure of claim 31 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

40. (Amended) A contact structure of claim 31 wherein the transparent conductive film comprises zinc oxide.

41. (Amended) A contact structure of claim 31 wherein the transparent conductive film comprises zinc oxide and indium oxide.

43. (Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing said first substrate;
a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit;

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a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and
a insulating film in contact with a side surface of said metallic film comprising the same material as that of the column-shape spacer,
wherein said connecting wiring, said column spacer, and said protecting film are formed over said first substrate,
wherein said insulating film is formed along with the length direction and the width direction of said lamination film, and
wherein said connecting wiring has a taper shape.

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45. (Amended) A contact structure of claim 43 wherein the insulating film is a resin film.

47. (Amended) A contact structure of claim 43 wherein the metallic film comprises Al.

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48. (Amended) A contact structure of claim 43 wherein the metallic film comprises W.

49. (Amended) A contact structure of claim 43 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

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51. (Amended) A contact structure of claim 43 wherein the transparent conductive film comprises zinc oxide.

52. (Amended) A contact structure of claim 43 wherein the transparent conductive film comprises zinc oxide and indium oxide.